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|---|---|--|
|   | Application No.   | Applicant(s)   |
| Nation of Allowahility  | 09/695,414  | ZHANG ET AL.   |
| Notice of Allowability  | Examiner  | Art Unit   |
|   | Evan Pert   | 2826   |
| The MAILING DATE of this communication appearance All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIOF of the Office or upon petition by the applicant. See 37 CFR 1.313  | (OR REMAINS) CLOSED in this or other appropriate communical IGHTS. This application is subje  | s application. If not included ation will be mailed in due course. THIS  |
| 1. This communication is responsive to the Appeal Brief filed   | August 25, 2003.  |  |
| 2. The allowed claim(s) is/are <u>1-18</u> .  |   |  |
| 3. $\boxtimes$ The drawings filed on <u>25 December 2003</u> are accepted by  | the Examiner.   | •  |
| <ul> <li>4.  Acknowledgment is made of a claim for foreign priority ur <ul> <li>a)  All b)  Some* c)  None of the:</li> <li>1.  Certified copies of the priority documents have</li> <li>2.  Certified copies of the priority documents have</li> <li>3.  Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)).</li> <li>* Certified copies not received:</li> </ul> </li> <li>Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.</li> <li>5.  A SUBSTITUTE OATH OR DECLARATION must be subm</li> </ul> | e been received. e been received in Application Note cuments have been received in to of this communication to file a red MENT of this application. | b. <u>08/420,472</u> This national stage application from the sply complying with the requirements  SER'S AMENDMENT or NOTICE OF |
| INFORMAL PATENT APPLICATION (PTO-152) which give  6.  CORRECTED DRAWINGS (as "replacement sheets") mus  (a) including changes required by the Notice of Draftspers  1) hereto or 2) to Paper No./Mail Date  (b) including changes required by the attached Examiner's   | st be submitted.<br>son's Patent Drawing Review(P   | TO-948) attached   |
| Paper No./Mail Date  Identifying indicia such as the application number (see 37 CFR 1, each sheet. Replacement sheet(s) should be labeled as such in the  |   |  |
| DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT   | sit of BIOLOGICAL MATERIA   | AL must be submitted. Note the   |
| Attachment(s)  1. ☑ Notice of References Cited (PTO-892)  2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)  3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date  4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material  | 6. ☐ Interview Summ<br>Paper No./Mail<br>08), 7. ☑ Examiner's Ame   | Date   |
|   |   | . •  |

# **DETAILED ACTION**

# Final Rejection and Appeal Brief

1. The final rejection (2-25-03) appealed by applicant in the Appeal Brief filed 8-25-03 is withdrawn.

### **EXAMINER'S AMENDMENT**

2. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows, to correct grammatical informalities:

- At page 9, last paragraph, second line, change "heating a substrate in a chamber" to –heating the substrate in the chamber--.
- At page 9, second-to-last paragraph, first line, change "a substrate is taken out from a chamber" to --the substrate is taken out from the chamber--.
- Change the title to:
- --Method of Forming Semiconductor Device by Crystallizing Amorphous Silicon and Forming Crystallization Promoting Material in the Same Chamber--.

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## Response to Arguments

3. Applicant argues that Liu et al. (US 5,147,826) do not disclose "a chamber," even though they disclose "nickel or palladium" (i.e. catalyst) being "thermally evaporated onto material" effecting patterning using a "shadow mask" [Example 2 at cols. 5-6]:

Applicant's argument that "there is no chamber in Liu et al." is scientifically puzzling since "thermal evaporation" of "metal" is notoriously well known to involve a vacuum chamber [e.g. see US 2,414,406, US 2,450,850, US 3,617,373, or Maissel et al. (Handbook of Thin Film Technology)].

If somehow "a chamber" is not inherent in Liu et al. for the "thermally evaporating" the metal, the existence of a vacuum "chamber" is most definitely *implicit*.

4. Applicant argues that it is improper to practice the methodology disclosed by Liu et al. (US 5,147,826) with the apparatus disclosed by Turner et al. (US 5,512,320), yet Liu et al. discloses a process having separate steps of 1) CVD of a-Si, 2) metal deposition by thermal evaporation (i.e. evaporation to deposit on a substrate in a vacuum chamber) and 3) RTA, that are a collection of process steps advantageously performed in a "multi-chamber integrated process system," of Maydan et al. for example, having vacuum process chambers and RTA (the Maydan et al. being incorporated by reference into Turner et al. per col. 1, lines 44-60 of Turner et al.).

Applicant's argument is not convincing that the process of Liu et al. would not be obvious to practice in a multi-chamber process, such as disclosed by Turner et al. (i.e. the apparatus Maydan et al.):

The generalized multi-chamber process tool of Maydan et al., having vacuum and RTA process chambers, has clear advantages when practicing the method of Liu et al., such as "improved productivity," "the concomitant advantage of a cleaner system," and "increased throughput" [col. 1, lines 44-60 of Turner et al.].

# Allowable Subject Matter

- 5. Claims 1-18 are allowed.
- 6. The following is an examiner's statement of reasons for allowance:

As now understood, the prior does not disclose or suggest applicant's method characterized by the claimed steps of "crystallizing" and "forming a crystallization promoting material" with both steps being successively performed in the *same* chamber (i.e. "continuously in the same chamber without taking out the substrate" per p. 6).

Applicant argues that Liu et al. do not disclose the limitation of "without...exposing to the air outside the chamber," which the examiner now realizes is equivalent to "performed continuously in the [same] chamber without taking out the substrate" [specification, p. 6, 3<sup>rd</sup> paragraph]. In other words, as applicant puts it:

Stated differently, the step of forming the crystallization promoting material and the step of crystallizing the semiconductor film are conducted successively in [the] same chamber without exposing the semiconductor film and the crystallization promoting material to the air outside the chamber. [Appeal Brief, top of p. 4].

The Liu et al. reference suggests a step of thermally evaporating palladium and nickel and a step of RTA, both steps implicitly being performed in chambers, yet they do not suggest how to accomplish these different steps in the *same* chamber:

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While a multi-chamber process tool would readily accommodate the different process steps of "thermally evaporating palladium" and "RTA" in Liu et al., by performing each step in a different chamber of the multi-chamber tool, a single chamber would not.

Notably, Applicant discloses that:

It is further desired that a multichamber system having a load chamber and an unload chamber is used instead of chamber 101, so that further throughput can be improved. [Specification, p. 12, 2<sup>nd</sup> paragraph, last sentence]

Therefore, applicant distinguishes a "multi-chamber system" from a single "chamber 101," meaning that the allowed claims, which are limited to using "a chamber" in which both "crystallizing" and "forming a crystallization promoting material" take place, are not enforceable against "crystallizing" and "forming a crystallization promoting material" in a "multi-chamber integrated process system" *unless* the acts of "crystallizing" and "forming a crystallization promoting material" are performed in "the same chamber" of the multi-chamber system.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

#### Conclusion

7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Evan Pert whose telephone number is 571-272-1969.

The examiner can normally be reached on M-F (7:30AM-3:30 PM).

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on 571-272-1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

ETP May 26, 2005

EVAN PERT
PRIMARY EXAMINER